



# RADSAGA



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# RADSAGA Training Workshop – March 2018





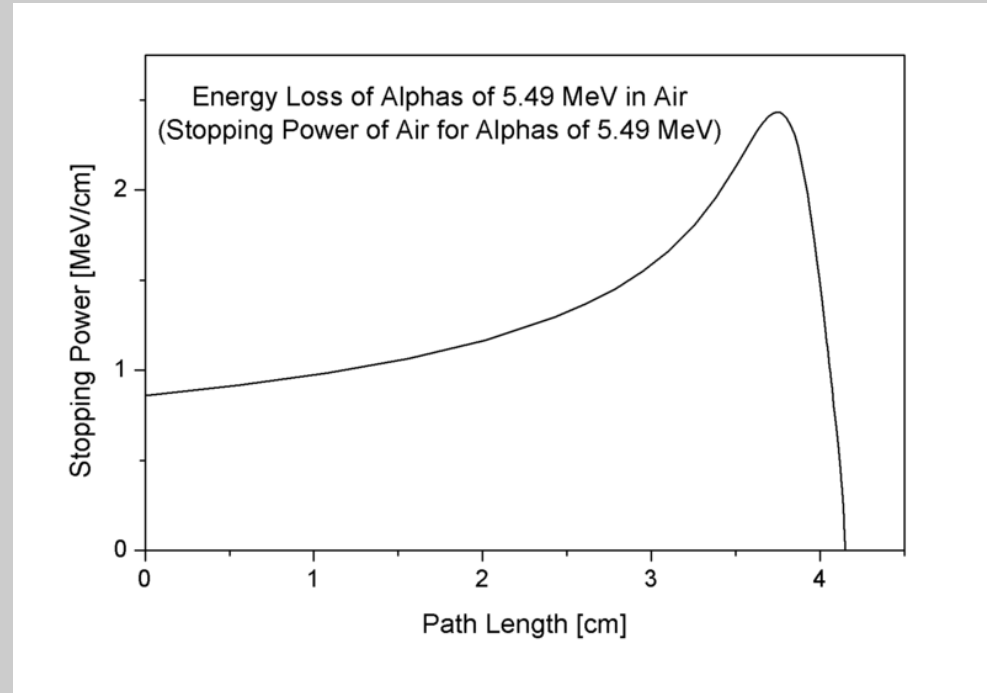
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# Key points

- ESR position no. 3 – Work Package 1
  - “Nano-dosimetry” – a new energy deposition metric
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- MC-tool including sub-LET threshold SEEs

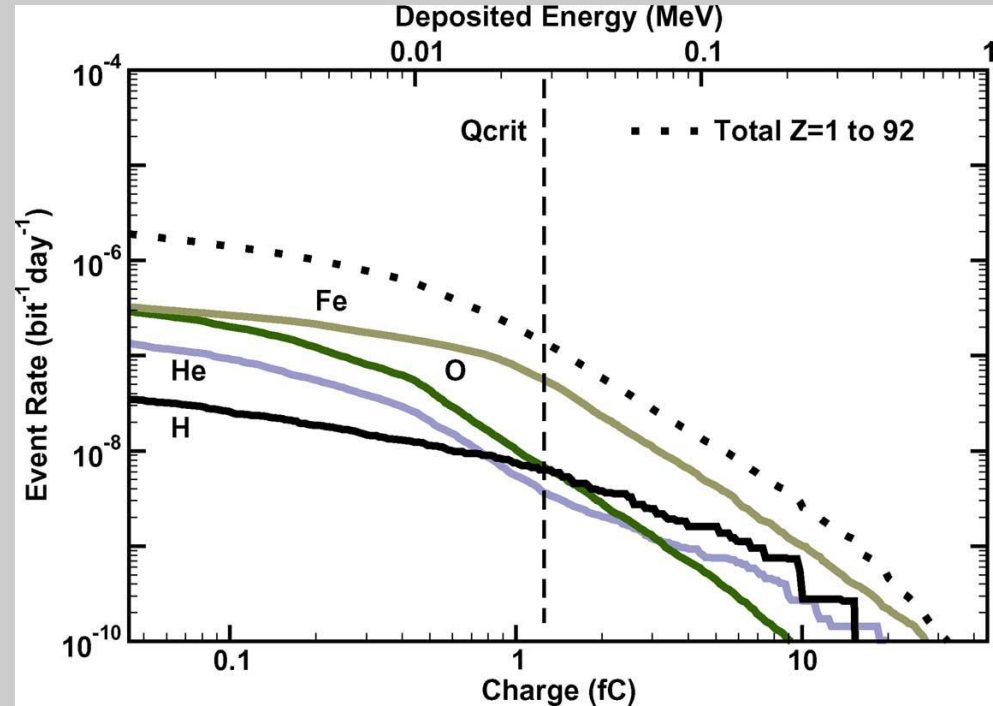
# LET describes only an average of deposited energy

- *Excitation and ionization of target/projectile atoms*
- *Electron capture*
- *Electromagnetic radiation*
- ***Nuclear reactions***
- ***Recoil loss ('nuclear stopping')***



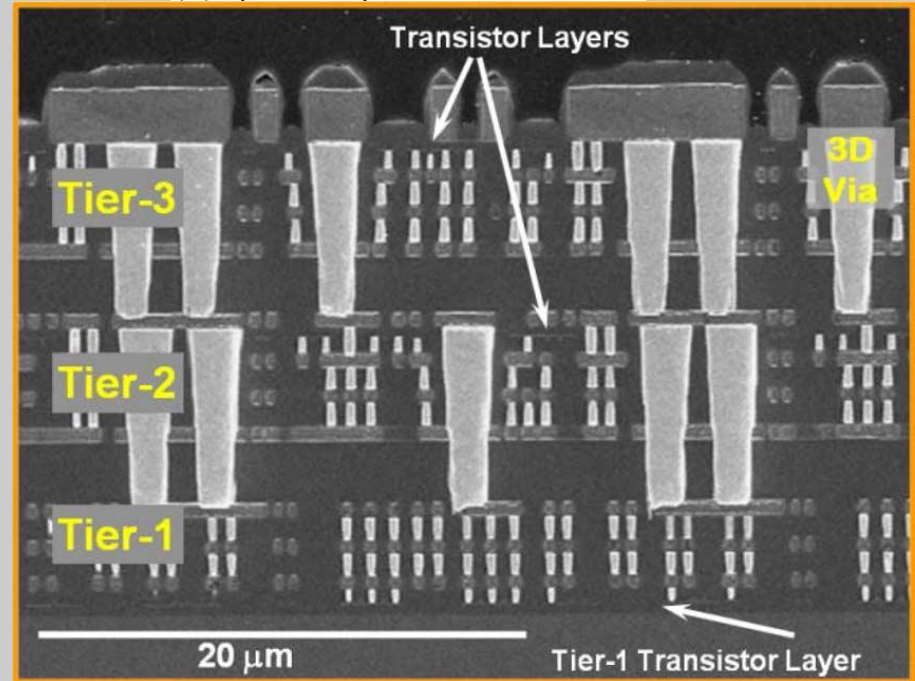
# A new energy deposition metric

- As technology keeps decreasing scaling, local variation of deposited charge may cause SEE on larger scale
- A new tool concerning nano-dose distribution and at the same time giving reasonable computing time is needed



# What do we need to take into account?

- Geometry – layout of IC, new tech. e.g. 3 DIC
- Materials – diverse component e.g. SiC, GaN
- Interfaces – possible drawbacks as technology keeps scaling



60 nm SOI, Device

# Summary

- We are looking for an energy deposition metric which takes into account phenomena occurring in nanoscale
- MC-simulation-tool with reasonable time-frame needed

## Upcoming campaigns

- Summer 2018 – KVI-CART
- Autumn 2018? – Uppsala University
- Autumn 2020? – CHARM at CERN



# Bibliography

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- [3] Brian D. Sierawski et al., “Impact of Low-Energy Proton Induced Upsets on Test Methods and Rate Predictions”, *IEEE Trans. Nucl. Sci.*, vol. 56, NO. 6 pp. 3085-3092, Dec. 2009
- [4] David F. Heide et al., “Single-Event-Upset Critical Charge Measurements and Modeling of 65 nm Silicon-on-Insulator Latches and Memory Cells”, *IEEE Trans. Nucl. Sci.*, vol. 53, NO. 6 pp. 3512-3517, Dec. 2006
- [5] Véronique Ferlet-Cavrois et al., “Single Event Transients in Digital CMOS—A Review”, *IEEE Trans. Nucl. Sci.*, vol. 60, NO. 3 pp. 1767-1790, Jun. 2013